



HC323T

APPLICATIONS

Switching Circuit , Interface Circuit.

ABSOLUTE MAXIMUM RATINGS ($T_a=25$)

T_{stg} —Storage Temperature..... -55~150

T_j —Junction Temperature.....150

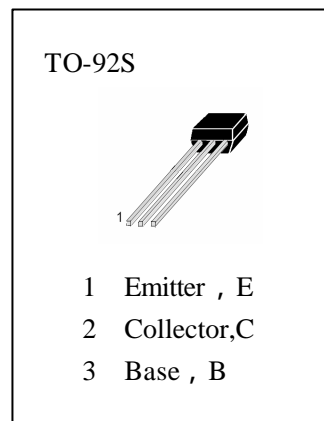
P_C —Collector Dissipation.....300mW

V_{CBO} —Collector-Base Voltage.....30V

V_{CEO} —Collector-Emitter Voltage.....15V

V_{EBO} —Emitter-Base Voltage.....5V

I_C —Collector Current.....600mA



ELECTRICAL CHARACTERISTICS ($T_a=25$)

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
BVCBO	Collector-Base Breakdown Voltage	30			V	$I_C=50 \mu A, I_E=0$
BVCEO	Collector-Emitter Breakdown Voltage	15			V	$I_C=1mA, I_B=0$
BVEBO	Emitter-Base Breakdown Voltage	5			V	$I_E=50 \mu A, I_C=0$
ICBO	Collector Cut-off Current			0.5	μA	$V_{CB}=20V, I_E=0$
IEBO	Emitter Cut-off Current			0.5	μA	$V_{EB}=4V, I_C=0$
HFE	DC Current Gain	100	250	600		$V_{CE}=5V, I_C=50mA$
$V_{CE(sat)}$	Collector- Emitter Saturation Voltage		40	80	mV	$I_C=50mA, I_B=2.5mA$
$V_I (off)$	Input Off Voltage	0.4	0.55	0.8	V	$V_{CE}=5V, I_C=0.1mA$
$V_I (on)$	Input On Voltage	0.6	0.8	1.5	V	$V_{CE}=0.2V, I_C=10mA$
R1	Input Resistor	1.64	2.2	2.86	K	
fr	Current Gain-Bandwidth Product		200		MHZ	$V_{CE}=10V, I_C=50mA, f=100MHZ$